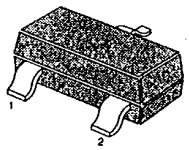
BCW70 PNP EPITAXIAL SILICON TRANSISTOR

T-29-19

GENERAL PURPOSE TRANSISTOR

SOT-23



1. Base 2. Emitter 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

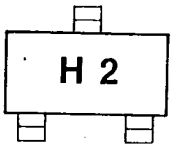
Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	Tstg	150	°C

• Refer to MMBT5086 for graphs

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=2.0mA, I_B=0	45		V
Collector-Emitter Breakdown Voltage	BV_{CES}	I_C=100μA, V_{EB}=0	50		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=10μA, I_C=0	5		V
Collector Cutoff Current	I_{CBO}	V_{CB}=20V, I_E=0		100	nA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=2.0mA	215	500	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=10mA, I_B=0.5mA		0.3	V
Base-Emitter On Voltage	V_{BE} (on)	I_C=2.0mA, V_{CE}=5V	0.6	0.75	V
Output Capacitance	Cob	V_{CB}=10V, I_E=0 f=1.0MHz		7.0	pF
Noise Figure	NF	I_C=0.2mA, V_{CE}=5.0V R_S=2.0KΩ, f=1.0KHz		10	dB

Marking



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